ABSTRACT OF THE DISCLOSURE

SILICIDED POLYSILICON SPACER FOR ENHANCED CONTACT AREA

[0070] An integrated circuit device having an increased source/drain contact area by a formed silicided polysilicon spacer. The polysilicon sidewall spacer is formed having a height less than seventy percent of said gate conductor height, and having a continuous surface silicide layer over the deep source and drain regions. The contact area is enhanced by the silicided polysilicon spacer.

Fig. 27